# Brewer Science® DUV 42P

248-nm Anti-Reflective Coating

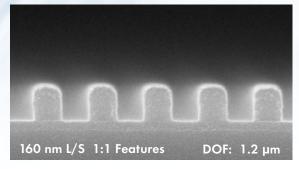


DUV 42P coating conserves etch budget and improves throughput in 248-nm lithography for ESCAP resist systems.

### **Benefits**

- Conserve etch budget with this conformal BARC that provides fast dry etching
- Increase tool uptime due to ultralow outgassing
- ▶ Compatible with ESCAP 248-nm photoresists

#### **DUV42P with JSR M230Y Resist**



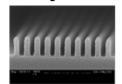
Resist thickness: 400 nm PAB: 130°C for 90 s PEB: 130°C for 90 s

BARC bake: 205°C for 60 s Exposure Dose: 18 mJ/cm<sup>2</sup>

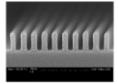
### **Exposure Latitude of DUV 42P Coatings**



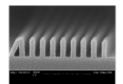
26 mJ/cm<sup>2</sup>



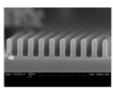
27 mJ/cm<sup>2</sup>



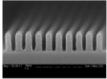
28 mJ/cm<sup>2</sup>



29 mJ/cm<sup>2</sup>



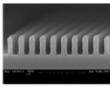
30 mJ/cm<sup>2</sup>



25 mJ/cm<sup>2</sup>

Resolution: 130 nm
Resist: JSR M91 Y
Film Thickness = 6100 Å
PAB = 130°C for 90 s
PEB = 120°C for 90 s
Focus = -0.2 µm
Canon EX3
NA = 0.60,  $\sigma$  = 0.65

\* \*Wafers patterned at JSR Corporation™



31 mJ/cm<sup>2</sup>



32 mJ/cm<sup>2</sup>

### **Material Properties**

### **Typical Properties**

lons (Al, Cu, Mg, Mn, K) < 25 ppb lons (Ca, Fe, Na) < 50 ppb Shelf Life at 21 °C ± 5 °C 12 months

### **Product-Specific Properties**

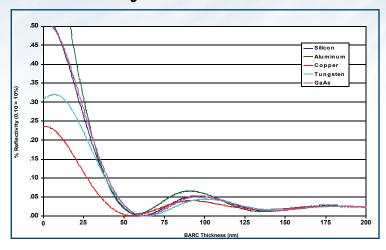
DUV 42P-6 coating:

Thickness at 2500 rpm, 205 °C 600 Å

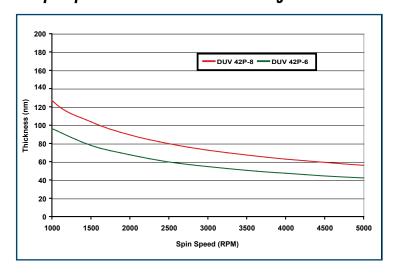
DUV 42P-8 coating:

Thickness at 2500 rpm, 205 °C 800 Å

## Reflectivity Curves on Various Substrates for DUV 42P Coatings



### Spin Speed Curves for DUV 42P Coatings



### **Process Recommendations**

#### Coat

DUV 42P coating is applied by spin coating. Apply with a dynamic dispense\* at 1000 to 4000 rpm and immediately ramp (no spread spin) to 2000 to 5000 rpm for 30 seconds. Use standard edge bead remover (EBR) and backside process at less than 1500 rpm with any standard EBR solvent, such as Brewer Science® Edge Bead Cleaner (EBC) Solvent. An adhesion promoter is not required.

\*Dispense speed optimization for specific equipment is required for thickness uniformity and defect reduction.

#### Bake

Single-stage hot plate bake at  $205^{\circ} \pm 20^{\circ}$ C for 60 seconds. Baking temperatures may need to be optimized to achieve the desired photoresist profile. A pre-bake of  $90^{\circ}$  to  $110^{\circ}$ C for 30 seconds will increase the planarization of the BARC.

### Resist Coat

Resist can be applied over the BARC without any modification to the standard resist spin-coating or baking process. An adhesion promoter is not required.

### **Exposure**

In most applications, exposure dose may need to be increased from that of stand-alone resist processes by 20% to 50% due to the reduction in reflected light from the substrate.

### Resist Develop

Use standard photoresist develop parameters.

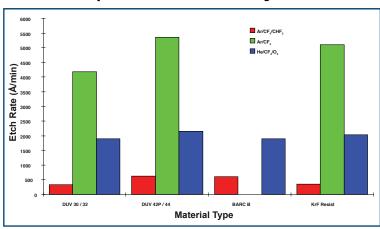
### Dry Etch

DUV 42P coating may be dry etched by a number of plasma etching methods in a range of etch gases including  $O_2$ ,  $O_2$ / CHF<sub>3</sub>/Ar,  $C_2$ F<sub>4</sub>, C1,  $N_2$ / $O_2$ ,  $O_2$ /HBr, and HCl.

### Stripping

DUV 42P coating can be removed by an oxidizing plasma or an oxidizing solvent stripping process such as ozone plasma stripping, Piranha® cleaning, or RCA cleaning.

### Etch Rate Comparison of DUV 42P Coatings



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